

ABSTRACT

Semiconductor devices and methods of fabricating semiconductor devices are disclosed. A disclosed semiconductor device comprises: a semiconductor substrate; an uppermost metal interconnect formed on the semiconductor substrate; an oxide layer formed on the substrate and the uppermost metal interconnect; an aluminum layer formed on the oxide layer; and a stress-relief layer formed on the aluminum layer to thereby prevent cracking of the passivation layer during a subsequent packaging process, to increase reliability of the passivation layer, and to prevent degradation of properties of the semiconductor device.